

Avionics RF Power LDMOS FET

The high power transistor part number ILD0912M550HV is designed for Avionics systems operating at 960-1215MHz. Operating at 10 μ s, 10% pulse conditions this LDMOS FET device supplies a minimum of 550 watts of power across the instantaneous operating bandwidth of 960-1215MHz. All devices are 100% screened for large signal RF parameters.



Silicon LDMOS FET

- High Power Gain
- Superior thermal stability

Class AB Operation

- Gate biased to $I_{DQ} = 40$ mA

Configuration

- Common Source

Gold Metal

- Maximum Reliability

Package

- Thermally enhanced
- Pb-free and RoHS-compliant

Epoxy Sealed Lid

- Gross Leak Qualified

RF Test Fixture

- Broadband
- Matched to 50 ohms
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning required

PRELIMINARY DATA

PRELIMINARY DATA

PRELIMINARY DATA

TBD

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	V_{DS}	--	70	V	--
BD	Gate-Source Voltage	V_{GS}	--	20	V	--
BD	Storage Temperature Range	T_{STG}	-55	+200	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	TBD	°C/W	$V_D=50V, I_{DQ}=40mA, T_F=25\pm5^\circ C, P_{OUT}=550W$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

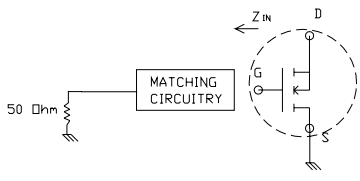
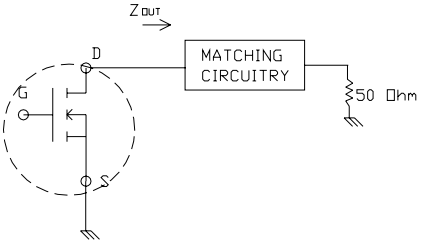
DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage	BV_{DSS}	100		V	$I_D = 40mA, V_{GS} = 0V, T_F = 25\pm5^\circ C$
100%	Drain Leakage Current	I_{DSS}		50	μA	$V_{DS} = 50V, V_{GS} = 0V, T_F = 25\pm5^\circ C$
100%	Gate Threshold Voltage	V_{GSTH2}	2.5	10	V	$I_D = 40mA, T_F = 25\pm5^\circ C$

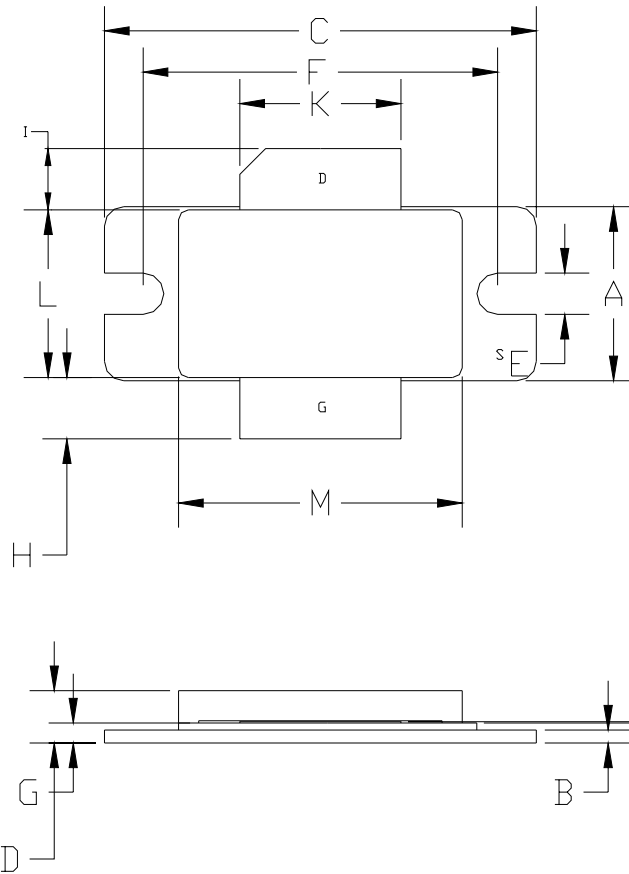
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	-18	-9	dB	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$.
BD	Maximum Overdrive	$P_{IN(MAX)}$	--	29	W	$V_{DD}=50V$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$.
100%	Power Gain	G_P	14	16	dB	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$.
100%	Output Power	P_{OUT}	550	872	W	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$.
100%	Drain Efficiency	η'_d	45		%	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$.
100%	Pulse Amplitude Droop	D	-0.5	+0.5	dB	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$.
100%	Stability into 2:1 VSWR	VSWR-S		2:1	--	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$. Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
BD	Load Mismatch Tolerance	LMT		20:1	--	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$. Rotate 20:1 output VSWR through 360° phase. Survival.
BD	Pulse Risetime	RT		60	ns	$V_{DD}=50V$, $P_{IN}=22W$, Pulse= $10\mu s$, 10%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=40mA$. Measure between 10% and 90% detected power points.
Note 1	F1 = 960-1090-1215 MHz.					
Note 2	Pulse format = $10\mu s$, 10%					
Note 3	T_F = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					

RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
960	TBD	TBD
1090	TBD	TBD
1215	TBD	TBD
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.535	0.545	13.58	13.84
B	0.035	0.045	0.89	1.14
C	1.335	1.345	33.90	34.16
D	0.147	0.177	3.73	4.50
E	0.123	0.133	3.12	3.37
F	1.095	1.105	27.81	28.06
G	0.057	0.067	--	--
H	0.170	0.210	4.32	5.33
I	0.170	0.210	4.32	5.33
J	0.003	0.006	0.08	0.15
K	0.495	0.505	12.57	12.82
L	0.514	0.524	13.05	13.31
M	0.871	0.889	22.12	22.58

PIN SCHEDULE	
D	DRAIN
S	SOURCE
G	GATE

RF TEST FIXTURE – ASSEMBLY AND PARTS LIST

TBD

RF TEST FIXTURE – CIRCUIT DIMENSIONS IN MILS

TBD

RF TEST FIXTURE – ELECTRICAL SCHEMATIC

TBD

DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

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